

ABSTRACT

The present invention are a method for producing a silicon wafer having a crystal orientation $<110>$ from a silicon single crystal ingot grown by a Floating Zone method (FZ method), wherein, at least, an FZ silicon single crystal ingot is grown by being made to be dislocation-free by Dash Necking method using a seed crystal having its crystal axis inclined at a specified angle from a crystal orientation $<110>$, and the grown FZ silicon single crystal ingot is sliced at the just angle of a crystal orientation $<110>$ to produce a silicon wafer having a crystal orientation $<110>$, and a silicon wafer produced by the method. Thereby, there are provided a method for producing a silicon wafer having a crystal orientation $<110>$ from a silicon single crystal ingot made to be dislocation-free at a high success rate by using Dash Necking method by FZ method, and a silicon wafer having an crystal orientation $<110>$.